

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	38	(gate same (wafer substrate) same resistance same (pattern\$3 etch\$3) same (dop\$3 implant\$3) (insulat\$3 dielectric) and (plug and contact) same (((monocrystal\$4 (mono near3 crystal\$4)) near5 silicon) ((single near5 crystal\$4) near silicon)) same (polycrystal\$3 (poly near3 crystal\$4))) same temperature same ((first second) (two double))). clm.	US-PGPU B	OR	ON	2005/09/17 11:06
L4	38	(gate same (wafer substrate) same resistance same (pattern\$3 etch\$3) same (dop\$3 implant\$3) (insulat\$3 dielectric) and (plug and contact) same (((monocrystal\$4 (mono near3 crystal\$4)) near5 silicon) ((single near5 crystal\$4) near silicon)) same (polycrystal\$3 (poly near3 crystal\$4))) same temperature same ((first second) (two double))). clm.	US-PGPU B	OR	ON	2005/09/17 11:06